

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a thin-film magnetic head comprising: a medium facing surface that faces toward a recording medium; a magnetoresistive element; a first shield layer and a second shield layer for shielding the magnetoresistive element, the shield layers having portions located on a side of the medium facing surface and opposed to each other, the magnetoresistive element being placed between these portions of the shield layers; a first shield gap film, provided between the magnetoresistive element and the first shield layer, for insulating the magnetoresistive element and the first shield layer from each other; and a second shield gap film, provided between the magnetoresistive element and the second shield layer, for insulating the magnetoresistive element and the second shield layer from each other; the method including the steps of:

forming the first shield layer;

forming the first shield gap film on the first shield layer;

forming the magnetoresistive element on the first shield gap film;

forming the second shield gap film on the magnetoresistive element; and

forming the second shield layer on the second shield gap film; wherein

at least one of the first and second shield gap films is formed by stacking a

plurality of insulating films formed by chemical vapor deposition, and

each of the insulating films has a thickness of 0.1 nm to 0.2 nm.

2. (Original) The method according to claim 1, wherein the insulating films formed by the chemical vapor deposition are alumina films.

3. (Original) The method according to claim 1, wherein the chemical vapor deposition is low pressure chemical vapor deposition.

4. (Original) The method according to claim 1, wherein the chemical vapor deposition is plasma chemical vapor deposition or atmospheric pressure chemical vapor deposition.

5. (Currently Amended) The method according to claim 1, wherein the insulating films formed by the chemical vapor deposition are formed through the use of a plurality of chambers such that a first one of the insulating films is formed in one of the chambers, and subsequently a next one of the insulating films is formed in another one of the chambers.

6. (Original) The method according to claim 1, wherein the insulating films formed by the chemical vapor deposition are formed through intermittently injecting a material for making the films.

7. (Currently Amended) The method according to claim 6, wherein the insulating films formed by the chemical vapor deposition are alumina films formed through intermittently injecting H_2O , N_2O or H_2O_2 which is the material a first material for making the films and $\text{Al}(\text{CH}_3)_3$ or AlCl_3 which is the material a second material for making the films in an alternate manner, wherein the first material is a material selected from the group consisting of H_2O , N_2O and H_2O_2 , and the second material is a material selected from the group consisting of $\text{Al}(\text{CH}_3)_3$ and AlCl_3 .

8. (Original) The method according to claim 1, wherein the insulating films formed by the chemical vapor deposition are formed at a temperature in a range of 100 to 350 °C.

9-32. (Canceled)